

Fig. 1. Schematic layout of the discriminator (dotted stripline printed on separate board).

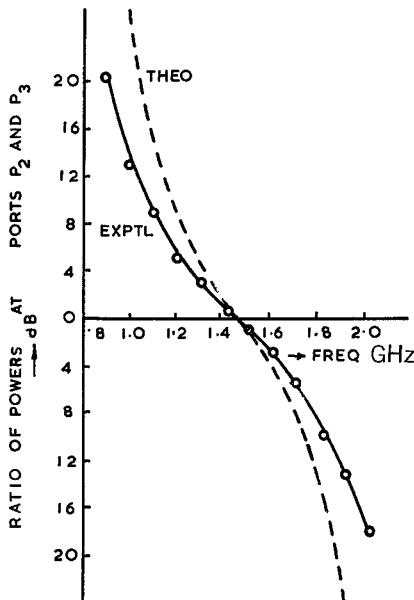


Fig. 2. Power discrimination characteristic of the L-band discriminator.

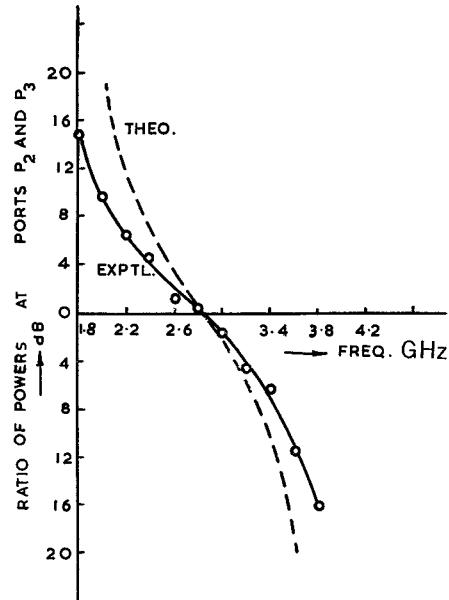


Fig. 3. Power discrimination characteristic of the S-band discriminator.

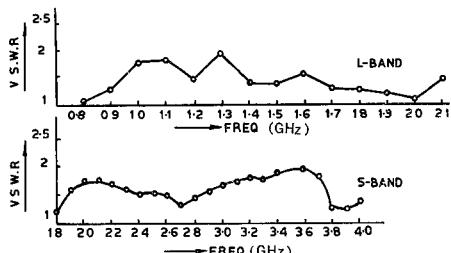


Fig. 4. VSWR characteristics of the L- and S-band discriminators.

the two units is less than 2.0, as shown in Fig. 4. The VSWR is somewhat higher than in normal stripline components on account of several relatively sharp changes in the stripline locations. The discrimination at the frequency ends is consequently reduced on this account and also due to the fact that epoxy board rather than teflon impregnated fiberglass board was used for printed striplines on account of the unavailability of the latter and this material is known to be more lossy at microwave frequencies. The discrimination is, however, adequate for usual discriminator applications. The power at the uncoupled port P_4 , in each of the units is more than 15 dB (mostly larger than 20 dB for L-band unit) below the incident power over the frequency band of operation.

ACKNOWLEDGMENT

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High-Q Microwave Filters Employing IMPATT Active Elements

During the course of switching studies¹ an unusually large transmission on/off ratio was obtained from an X-band single PIN diode switch operating in the milliwatt range. The phenomenon is attributed to the generation of a microwave negative resistance of the IMPATT type (*Impact Avalanche Transit Time*) when reverse bias current flows. This negative resistance cancels the normal series R_S loss of the diode and associated contact losses giving a true wideband zero loss waveguide switch.

Figure 1 shows the lumped element equivalent circuit. Under forward bias the total diode impedance (Z) approximates a short circuit with the package capacity (C_p) and the contacting spring (L_s) in parallel resonance creating a bandpass circuit. When the diode is appreciably reverse biased (but not into breakdown) the diode impedance becomes a large capacitive reactance allowing the inductive stub and the package capacity to be series resonant. Figure 2 shows the typical "off" transmission characteristics. The dotted transmission loss characteristic of Fig. 2 represents the maximum possible loss for this circuit with passive elements found experimentally by replacing the encapsulated diode with an open circuit package. When 2 mA of reverse current is drawn, the transmission loss jumps to 55 dB as shown in Fig. 3, an increase

TABLE I

L-Band Unit		S-Band Unit	
Frequency GHz	θ Radians	Frequency GHz	θ Radians
1.0	0.1386	2.0	0.2287
1.1	0.1638	2.2	0.1944
1.2	0.1275	2.4	0.1104
1.3	0.0466	2.6	0.1384
1.4	0.0256	2.8	0.0286
1.5	-0.044	3.0	-0.0371
1.6	-0.1339	3.2	-0.0417
1.7	-0.1364	3.4	-0.1374
1.8	-0.1217	3.6	-0.1204
1.9	-0.1987	3.8	-0.1034

Manuscript received September 21, 1966.

¹ R. W. Dawson and B. C. De Loach, "A low loss 1 nanosecond 1 watt X-band switch," *Symp. D'gest—Internat'l Symp. on Microwave Theory and Techniques*, 1966.

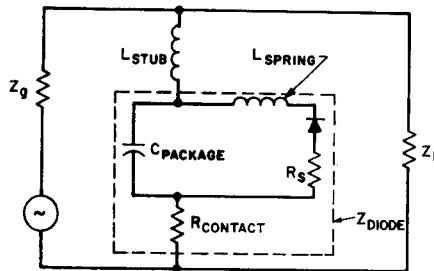


Fig. 1. Lumped element equivalent circuit.

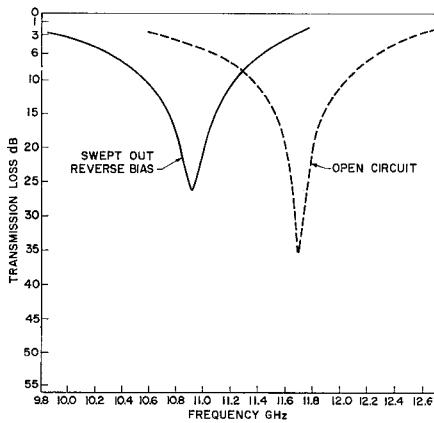


Fig. 2. "Off" transmission characteristic under high reverse bias (solid line) with an "open circuit" reference (dashed line) corresponding to "lossless" diode performance.

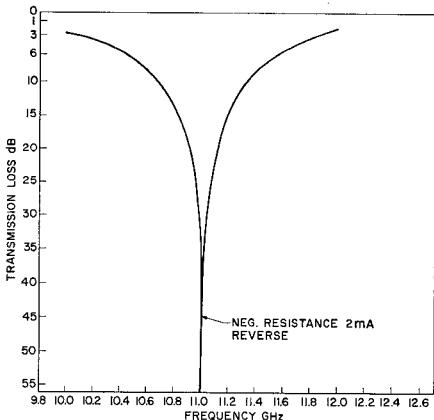


Fig. 3. "Off" transmission characteristic when reverse breakdown voltage is exceeded to the extent that 2 mA of current are flowing.

which can only result from cancellation of the various resistance losses.

An equally dramatic demonstration of the introduction of negative resistance to the circuit under IMPATT operation is to observe the reflection coefficient. At normal 30 to 35 dB transmission loss the return loss is very close to zero but as the diode avalanche current is increased from 2 to 5 mA the return loss passes through zero and reverses sign since more power is contained in the reflected wave than in the incident wave. In both transmission and reflection operations the filter characteristic is very sensitive to the amount of reverse current.

The increase of circuit Q is accompanied by an additional noise over normal passive

operation and a reduction in effective bandwidth. All results described were obtained with CW measurements. Equivalent power relationships were also secured under bias pulse operation; however, pulse width reproducibility was reduced. Regular passive operation faithfully reproduced a triangular input bias pulse of 1×10^{-9} s at the base with approximately equal rise and fall times. When the diode was pulsed into IMPATT operation with the same shaped triangular input pulse the reproduced reflected pulse is stretched out to approximately 5×10^{-9} s. The RF input power level was approximately 0 dBm for all described tests. An appreciable increase of input power prevented successful operation.

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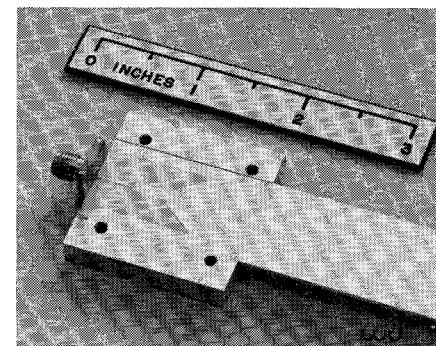


Fig. 1.

impedance would be the same and independent of frequency. Particularly distressing is the rapid change in impedance near the guide cutoff frequency. This rapid change was found to restrict the useful low-frequency limit of the transition to about 20 percent above the guide cutoff frequency. Normally waveguide can be used to about 13 percent above cutoff.

The final design of the transition was reached by empirical modifications using swept frequency techniques. The initial configuration was a two-step quarter-wavelength microstrip transformer designed to transform 50 ohms to the average guide impedance, the power-voltage (Z_{WV}) impedance of the guide being used.² The transformer was followed by a quarter-wavelength taper from a width corresponding to a microstrip impedance equal to the average guide impedance³ (see Fig. 1). The net length of the transition was three quarter-wavelengths long.

Figure 3 is a cutaway drawing of the assembled transition. Adjustment of the shorting bar serves to equalize the VSWR over the frequency band. In particular, movement in the direction of the connector decreases the VSWR at the lower band edge with a corresponding increase at the higher frequencies. Swept data for the optimized transition is shown in Fig. 4. This data is for a $0.060 \times 0.930 \times 10$ inch guide of $K=15$ dielectric, with a transition at each end.³ The fine structure of the VSWR is due to the many wavelengths between transitions. The peak VSWR of the whole assembly is slightly greater than 1.5 to 1. The performance of the transition remains good above the TE_{20} cutoff frequency which is at 3.26 GHz for the case shown. Similar transitions were made for guide thickness as small as 0.038 inch. The same technique should be useful in making TEM transitions to guides of higher dielectric constants such as titanium dioxide of $K=96$ or for multi octave frequency bands using the dielectric-filled guide equivalent to ridge guide.

² Design curves for linewidths of microstrip transmission line on Al_2O_3 substrates are available. (B. T. Vincent, Jr., "Ceramic microstrip for microwave hybrid integrated circuits," *G-MTT Symp. Digest*, 1966.) In first approximation these curves can be used for other dielectric constants by multiplying the required impedance and dividing the wavelength by the square root of the ratio of the two dielectric constants.

³ Subsequent Boonton bridge measurements on this dielectric material indicate that the actual dielectric constant was 11.9 and not its nominal value of 15. Thus the actual guide cutoff was 1.83 GHz and not the calculated value of 1.63 GHz based on a dielectric constant of 15. This would indicate that the transition is usable to within 6 percent of cutoff.

Manuscript received September 30, 1966.

¹ E. L. Ginzton, *Microwave Measurements*, New York: McGraw-Hill, 1957, p. 205, equations 4.7, 4.8, and 4.9.